

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a TO92 plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

## 2. Features and benefits

- High blocking voltage capability
- Very sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits

## 3. Applications

- Industrial process control
- General purpose low power motor control
- Home appliances
- Low power AC Fan controllers

## 4. Quick reference data

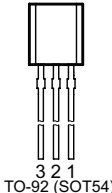
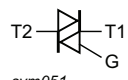
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Absolute maximum rating</b>						
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 45\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	1	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	8	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	8.5	A
$T_j$	junction temperature		-	-	125	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	7	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	10	mA
$V_T$	on-state voltage	$I_T = 1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	1.3	1.6	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536 \text{ V}$ ; $T_j = 110 \text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a>	20	-	-	V/ $\mu\text{s}$
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400 \text{ V}$ ; $T_j = 110 \text{ }^\circ\text{C}$ ; $di_{com}/dt = 0.44 \text{ A/ms}$ ; $I_T = 1 \text{ A}$ ; gate open circuit	1	-	-	V/ $\mu\text{s}$

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 <p>TO-92 (SOT54)</p>	 <p>sym051</p>
2	G	gate		
3	T1	main terminal 1		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
Z0107NA	TO92	Z0107NA,412	Bulk	1000	SOT54	14-Nov-2013
Z0107NA	TO92	Z0107NA,126	Ammo	2000	SOT54 wide pitch	14-Nov-2013
Z0107NA	TO92	Z0107NA,116	Reel	2000	SOT54 wide pitch	14-Nov-2013
Z0107NA/DG	TO92	Z0107NA/DG,116	Reel	2000	SOT54 wide pitch	14-Nov-2013

## 7. Marking

Table 4. Marking codes

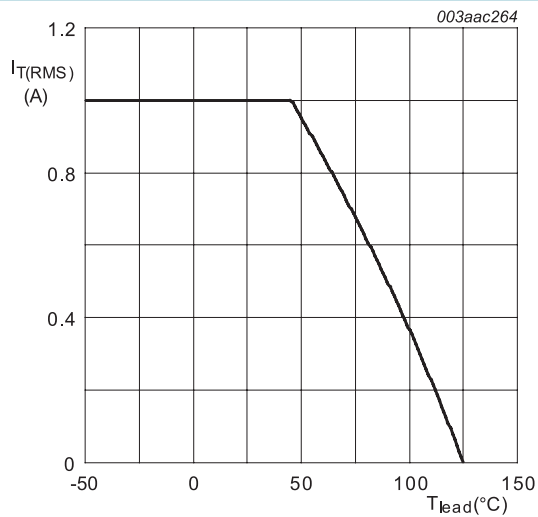
Type number	Marking codes
Z0107NA	0107NA

## 8. Limiting values

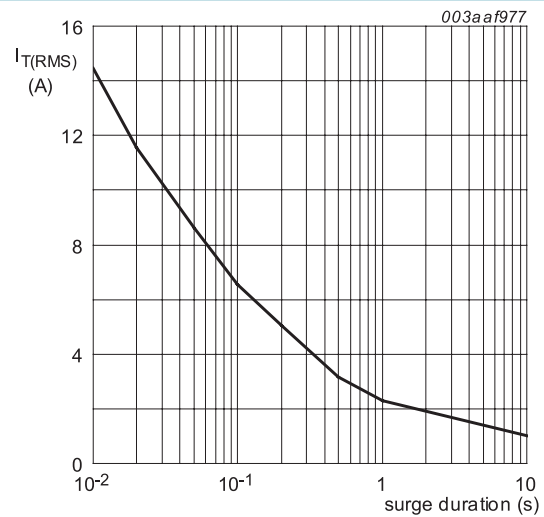
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 45\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	1	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	8	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	8.5	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	0.32	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 10\text{ mA}$	-	50	A/ $\mu$ s
		$I_G = 10\text{ mA}$	-	50	A/ $\mu$ s
		$I_G = 14\text{ mA}$	-	20	A/ $\mu$ s
		$I_G = 10\text{ mA}$	-	50	A/ $\mu$ s
$I_{GM}$	peak gate current		-	1	A
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C



**Fig. 1. RMS on-state current as a function of lead temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{lead} = 45\text{ °C}$   
**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

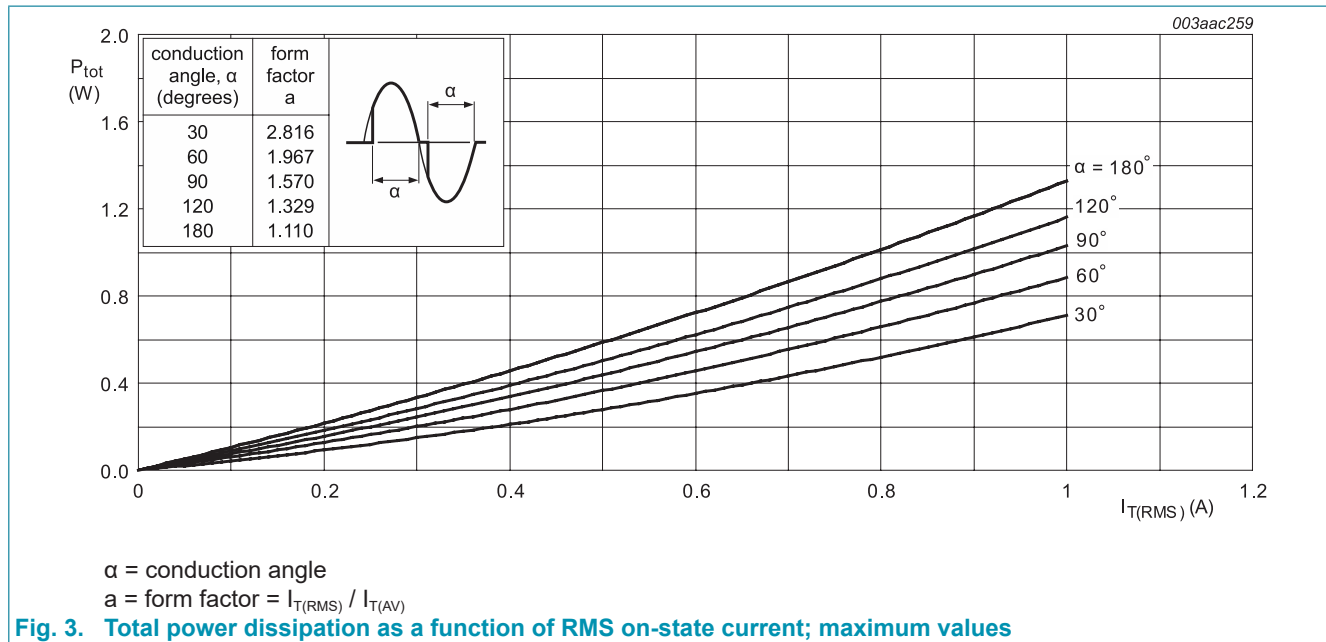


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

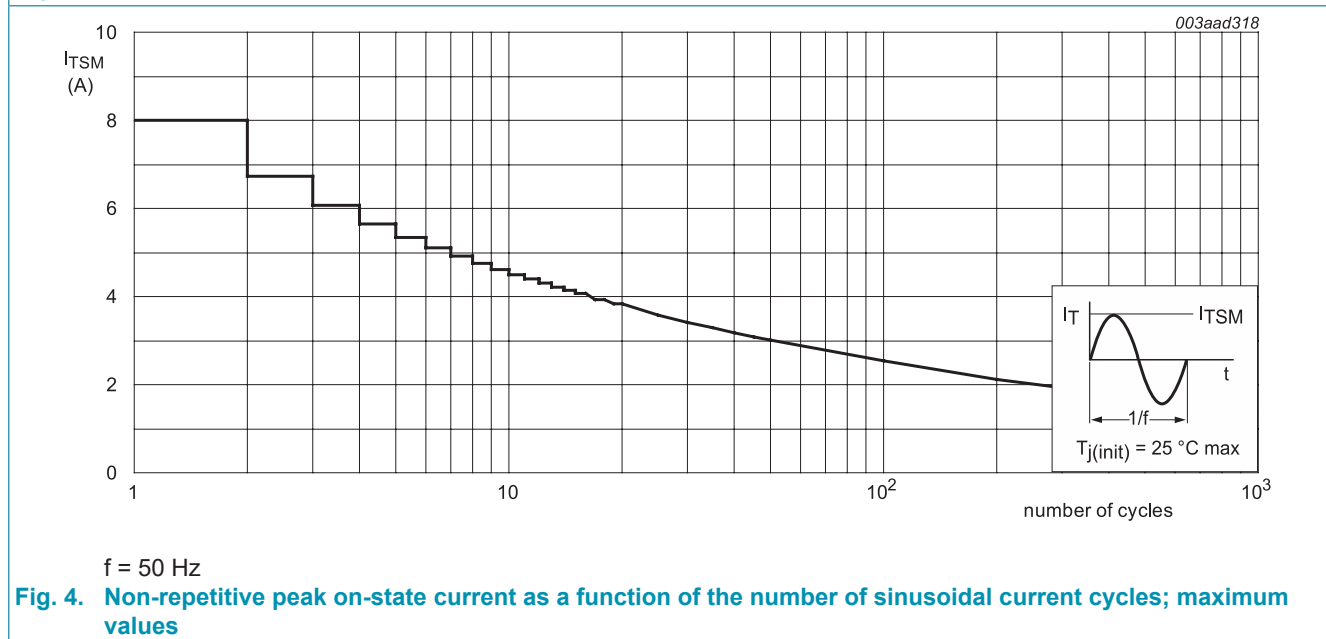


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

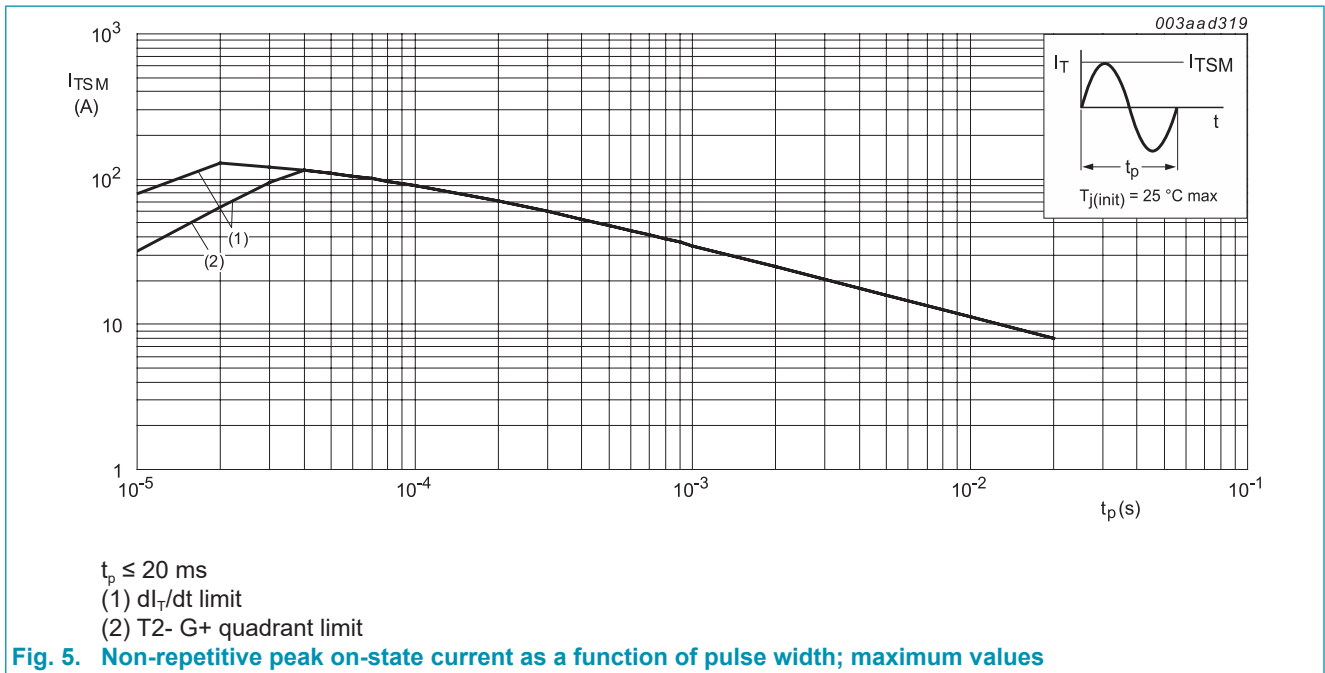


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; <a href="#">Fig. 6</a>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	full cycle; printed circuit board: lead length = 4 mm	-	150	-	K/W

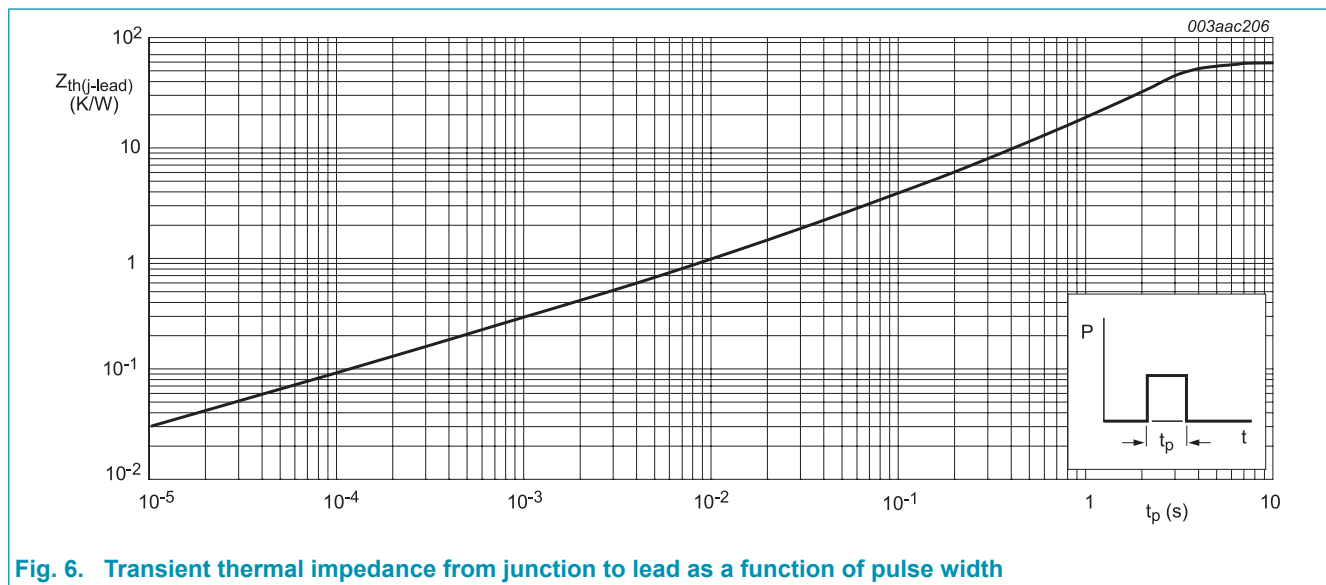


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	7	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	20	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	10	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	10	mA
$V_T$	on-state voltage	$I_T = 1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	-	1	V
		$V_D = 800\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 125\text{ °C}$	0.2	-	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_J = 125\text{ °C}$	-	-	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 110\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a>	20	-	-	V/ $\mu$ s
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400\text{ V}$ ; $T_J = 110\text{ °C}$ ; $dI_{com}/dt = 0.44\text{ A/ms}$ ; $I_T = 1\text{ A}$ ; gate open circuit	1	-	-	V/ $\mu$ s

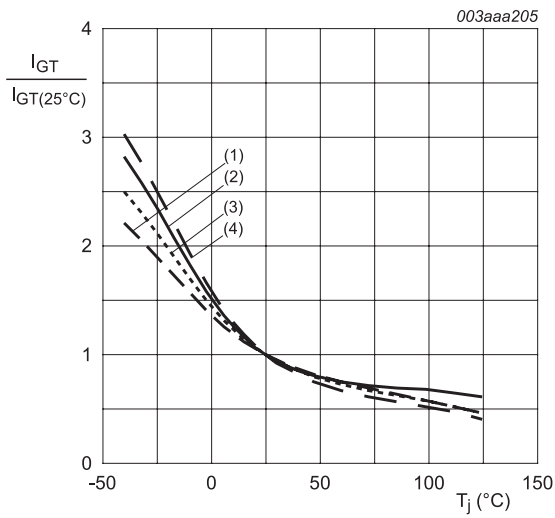


Fig. 7. Normalized gate trigger current as a function of junction temperature

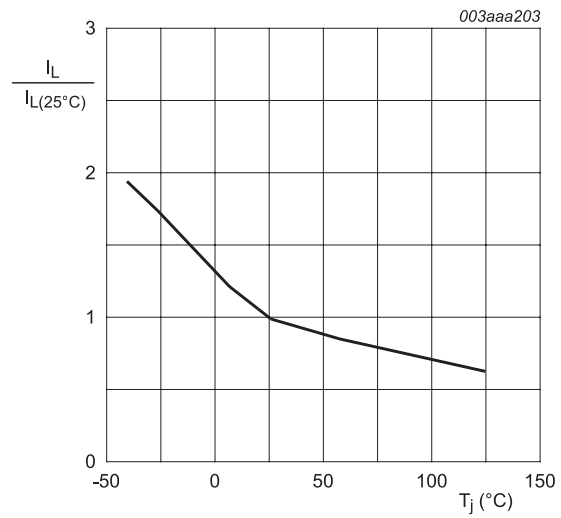


Fig. 8. Normalized latching current as a function of junction temperature

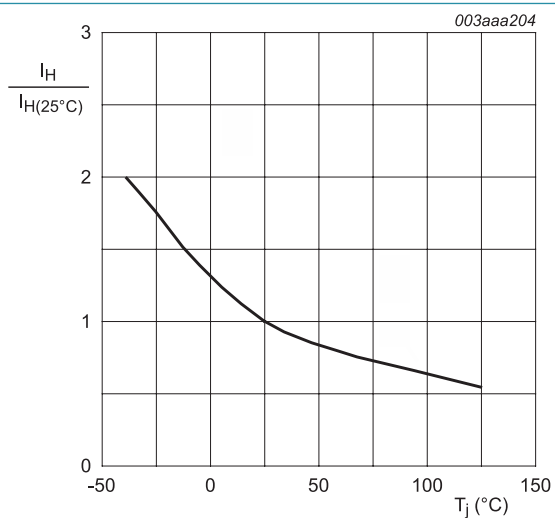


Fig. 9. Normalized holding current as a function of junction temperature

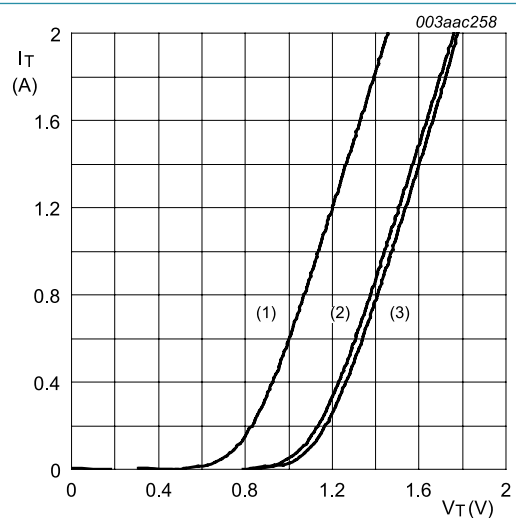


Fig. 10. On-state current as a function of on-state voltage

$V_o = 1.13 \text{ V}; R_s = 0.31 \Omega$



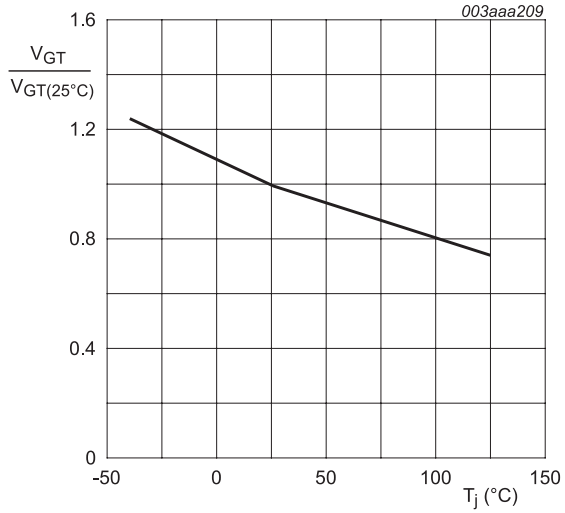
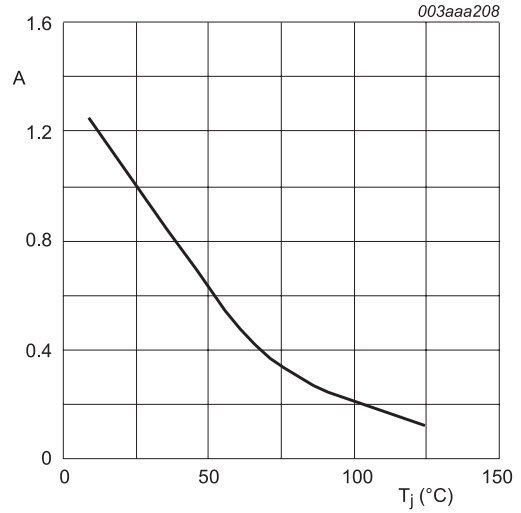


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

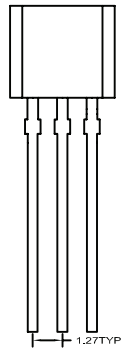


$$A = \frac{dV_D(T_j \text{ } ^\circ\text{C})/dt}{dV_D(25^\circ\text{C})/dt}$$

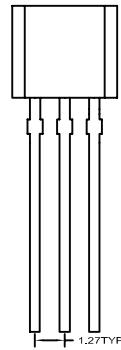
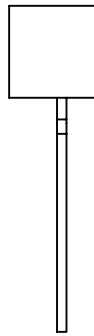
Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

## 11. Package outline

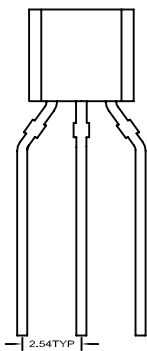
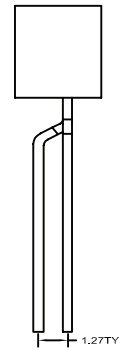
### SOT54 PACKAGE OUTLINE



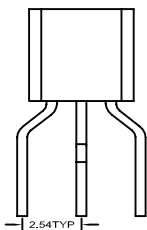
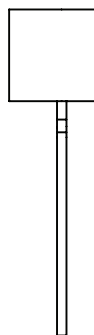
SOT54  
Bulk Pack - 412



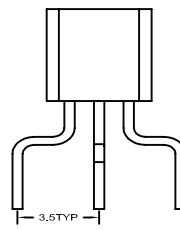
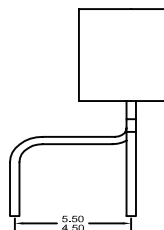
SOT54 LEADS ON CIRCLE  
Bulk Pack - 112



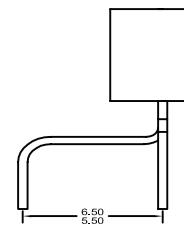
SOT54 WIDE PITCH  
Tape/ Reel Pack - 116  
Ammo Pack - 126



SOT54 LEAD BEND L01  
Bulk Pack - 412



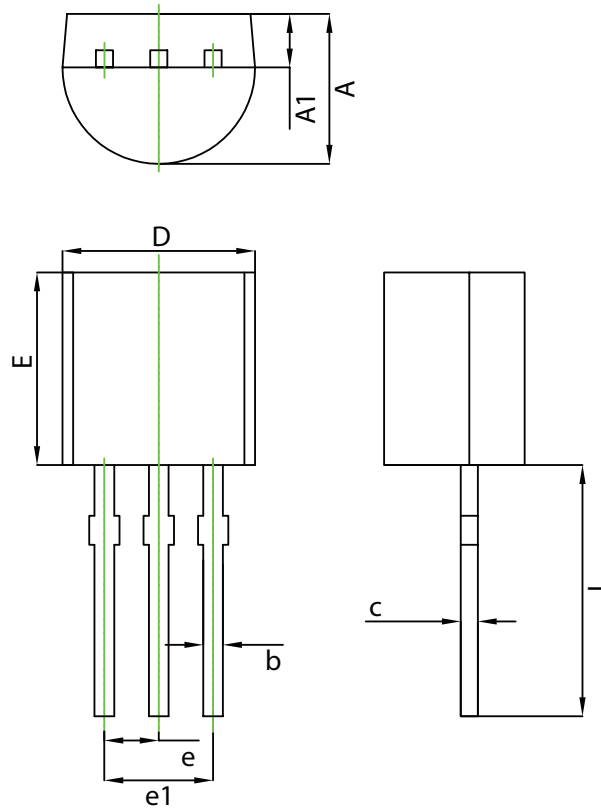
SOT54 LEAD BEND L02  
Bulk Pack - 412



Remark: Detailed dimensions refer to POD drawing.

Plastic single-ended leaded(through hole) package; 3 leads

TO92



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
E	4.300	4.700	0.169	0.185
e	1.270 TYP.		0.050 TYP.	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 17 November 2021

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